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November 2013

### **FQP24N08**

# N-Channel QFET $^{\circledR}$ MOSFET 80 V, 24 A, 60 m $\Omega$

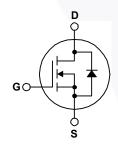
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### **Features**

- 24 A, 80 V,  $R_{DS(on)}$  = 60 m $\Omega$  (Max.) @ $V_{GS}$  = 10 V,  $I_D$ = 12 A
- Low Gate Charge (Typ. 19 nC)
- · Low Crss (Typ. 50 pF)
- · 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQP24N08	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		80	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		24	Α
	- Continuous (T <sub>C</sub> = 100°C)		17	А
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	96	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note		230	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	24	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note		6.5	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		75	W
	- Derate above 25°C		0.5	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds	300	°C	

#### **Thermal Characteristics**

Symbol	Parameter	FQP24N08	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.0	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

### **Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP24N08	FQP24N08	TO-220	Tube	N/A	N/A	50 units

### Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.08		V/°C
I <sub>DSS</sub>	Zoro Cato Voltago Prain Current	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V			1	μΑ
Zei	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 64 V, T <sub>C</sub> = 150°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A		0.048	0.06	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 12 A		12		S
Dynam	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		580	750	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		210	270	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			50	65	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V = 40 V L = 24 A		10	30	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 40 \text{ V}, I_{D} = 24 \text{ A},$ $R_{G} = 25 \Omega$		105	220	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	T(G - 20 22		30	70	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		35	80	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 64 V, I <sub>D</sub> = 24 A,		19	25	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		4.2		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		9.6	,	nC
1	Source Diode Characteristics and Ma	kimum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				24	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward	Current			96	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 24 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time			63		ns
Q <sub>rr</sub>	Reverse Recovery Charge dI <sub>F</sub> / dt = 100 A/μs			130		nC

#### Notes:

- Notes: Notes: Notes: Notes: A Repetitive Rating: Pulse width limited by maximum junction temperature. 
  2. L = 0.55 mH,  $I_{AS}$  = 24 A,  $V_{DD}$  = 25 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C. 
  3.  $I_{SD}$  ≤ 24 A, di/dt ≤ 300 A/µs,  $V_{DD}$  ≤ BV<sub>DSS</sub>, starting  $T_{J}$  = 25°C. 
  4. Essentially independent of operating temperature.

### **Typical Characteristics**

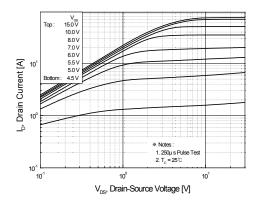


Figure 1. On-Region Characteristics

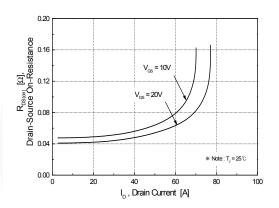


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

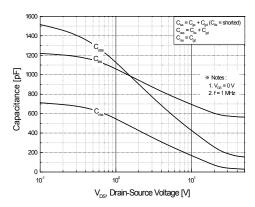


Figure 5. Capacitance Characteristics

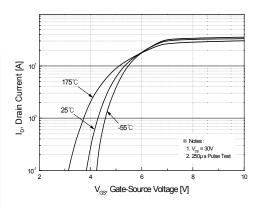


Figure 2. Transfer Characteristics

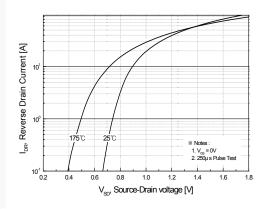


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

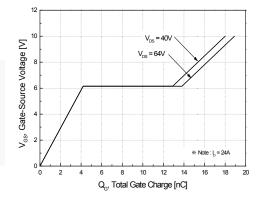


Figure 6. Gate Charge Characteristics

### Typical Characteristics (Continued)

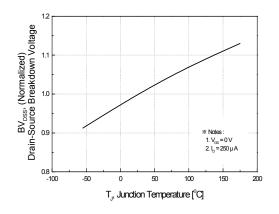


Figure 7. Breakdown Voltage Variation vs. Temperature

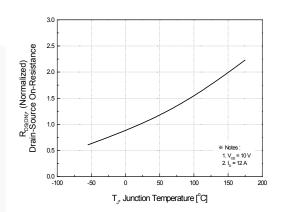


Figure 8. On-Resistance Variation vs. Temperature

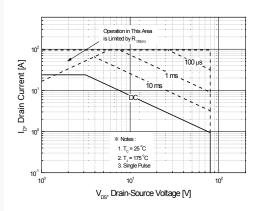


Figure 9. Maximum Safe Operating Area

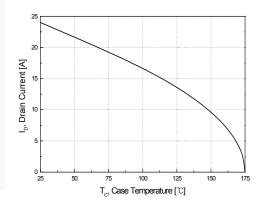


Figure 10. Maximum Drain Current vs. Case Temperature

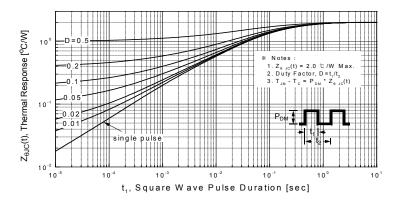


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

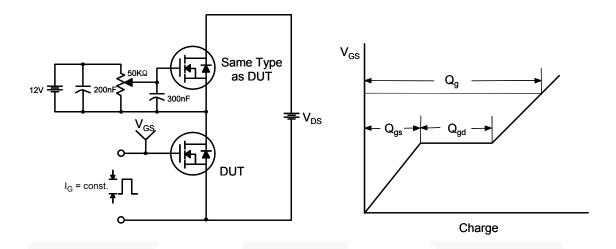


Figure 13. Resistive Switching Test Circuit & Waveforms

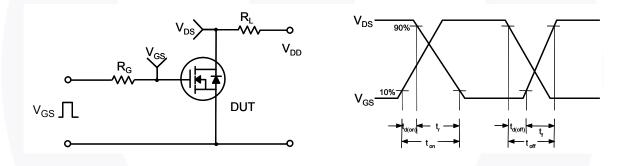
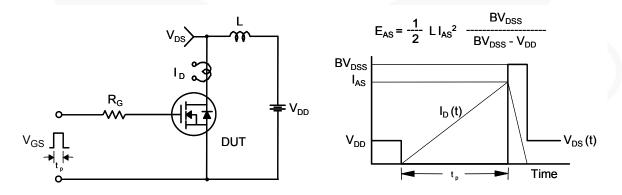


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



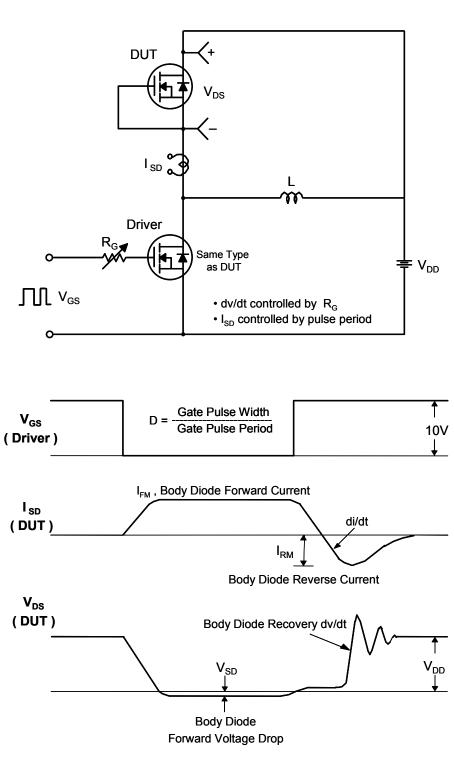


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

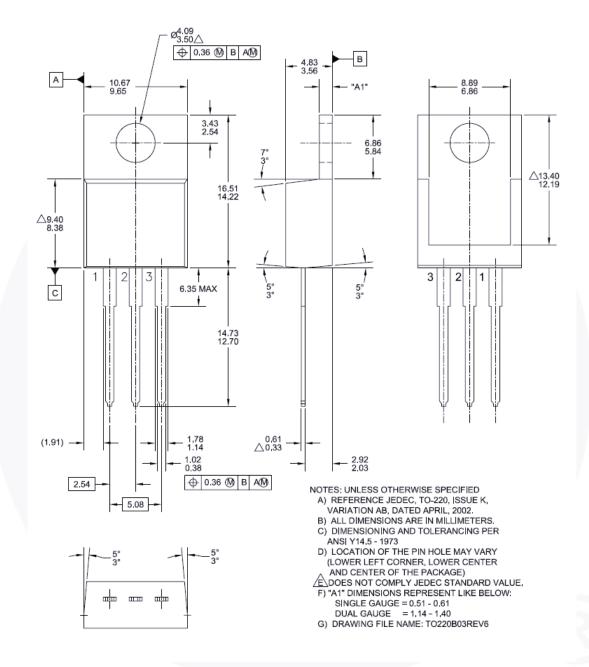


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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Dimension in Millimeters





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